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Xu, Zhangcheng; Birkedal, Dan; Juhl, Michael; Hvam, Jørn Märcher

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Submonolayer InGaAs/GaAs quantum-dot lasers with high modal gain and zero-linewidth enhancement factor

Zhangcheng Xu\textsuperscript{a)}

The Key Lab of Advanced Technique and Fabrication for Weak-Light Nonlinear Photonics Materials, Ministry of Education, Nankai University, Tianjin 300071, P.R. China and Research Center COM, Technical University of Denmark, DK-2800, Lyngby, Denmark

Dan Birkedal, Michael Juhl, and Jørn M. Hvam

Research Center COM, Technical University of Denmark, DK-2800, Lyngby, Denmark

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The gain spectra of a submonolayer (SML) InGaAs/GaAs quantum dot (QD) laser working at 30°C were measured using the Hakki–Paoli method. It is found that the maximum modal gain of QD ground states is as high as 44 cm\textsuperscript{−1} and no gain saturation occurs below the threshold at the lasing wavelength of 964.1 nm. When the injection current is about 0.98 times the threshold, the gain spectrum becomes symmetric with respect to the lasing wavelength, and zero-linewidth enhancement factor is observed. These properties are attributed to the high density and the high uniformity of SML QDs in our laser diode. © 2004 American Institute of Physics.

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As an alternative growth mode to the conventional Straniski–Krastanow (SK) mode of growing self-assembled semiconductor quantum dot (QDs), submonolayer (SML) deposition has recently received some attention, due to its potential of fabricating QDs with high density and high uniformity.\textsuperscript{1–3} The deposition of a short-period InAs/GaAs superlattice on a GaAs (100) surface, with an InAs effective thickness of less than 1 monolayer (ML) and a suitable number of periods, results in the formation of nanometer scale (In, Ga) As QDs of a non-SK class.\textsuperscript{4} Recently, an SML InGaAs/GaAs QD heterostructure is verified to be a QD quantum-well (QW) structure, i.e., the indium-rich QDs are embedded in a lateral quantum well (QW) with lower indium content.\textsuperscript{5,6} High-power lasers with SML InGaAs/GaAs QDs as the active region have been demonstrated.\textsuperscript{4,7,8} Although the gain properties of SK InGaAs/GaAs QD lasers have not been reported, in this letter, we report the measurement of the gain spectra and the determination of the linewidth enhancement factor of an SML InGaAs/GaAs QD laser.

The epitaxial structure was grown by solid-source molecular-beam epitaxy on an n\textsuperscript{+}-doped GaAs (100) substrate. It consists of an n-type (10\textsuperscript{18} cm\textsuperscript{−3}) 0.5 μm thick GaAs buffer, a 1.5 μm thick n-type (10\textsuperscript{18} cm\textsuperscript{−3}) Al\textsubscript{0.2}Ga\textsubscript{0.8}As lower cladding layer, 200 nm thick GaAs confining layers (n =10\textsuperscript{17} cm\textsuperscript{−3} and p=10\textsuperscript{17} cm\textsuperscript{−3}) surrounding the laser active region, a 1.5 μm p-type (10\textsuperscript{18} cm\textsuperscript{−3}) upper cladding layer, and a p\textsuperscript{+}-doped (10\textsuperscript{19} cm\textsuperscript{−3}) 200 nm thick GaAs cap for ohmic contact. In the active region, 0.5 ML InAs and 2.5 ML GaAs were alternately deposited at 500°C with 10 periods, to form the SML QD layer. All the other layers were grown at 600°C. A photoluminescence signal from the QD ground states is still observable at room temperature, for an SML InGaAs/GaAs QD sample grown under the same conditions as the QDs in the laser structure. A broad-area edge-emitting SML InGaAs/GaAs QD laser with a 100 μm wide stripe, a 628 μm long cavity and uncoated facets, was fabricated and mounted with the n-side down on a thermoelectric cooler. The emitted light is dispersed by a high-resolution spectrometer and detected by a Si charge-coupled-device. Far-field spatial filtering is employed to remove the interference of a large number of lateral modes.\textsuperscript{10} Measurements were performed at 30°C, under pulsed excitation to eliminate additional heating. The pulse width is 0.2 μs, and the duty cycle is 0.1%.

The gain spectrum is measured using the Hakki–Paoli method.\textsuperscript{11} The difference between the modal gain \(g_{\text{mod}}\) and the internal loss \(\alpha_i\), i.e., the net modal gain \(g_{\text{net}}\), is given by

\[
g_{\text{net}} = \frac{1}{L} \ln \left( \frac{r^{1/2} - 1}{r^{1/2} + 1} \right) - \frac{1}{2L} \ln(R_1R_2),
\]

where \(L\) is the cavity length, \(R_1\) and \(R_2\) are the power reflectivity of the cleaved facets, and \(r\) is the peak-to-valley ratio.

FIG. 1. The electroluminescence spectra measured from the side of an SML InGaAs/GaAs QD laser, at 30°C. The threshold current is 235 mA, and the lasing wavelength is 964.1 nm.
of the Fabry–Perot oscillations in the intensity of the light emitted from the device. In the long-wavelength limit, $g_{\text{mod}}$ approaches zero, therefore, the measured $g_{\text{net}}$ will be equal to $-\alpha$, from which the spectrum of the modal gain can be obtained.\textsuperscript{20} Figure 1 shows the typical emission spectra at 200 mA, 230 mA, and 235 mA ($I_{\text{th}}$). Figure 2 shows the net modal gain spectra at several currents. The mirror reflectivity represents, a very high value of the modal gain from the ground states of a single sheet of self-assembled QDs.

Another important parameter of semiconductor lasers is the linewidth enhancement factor ($\alpha$-factor). In high-power semiconductor laser applications, the $\alpha$-factor must be minimized in order to reduce filamentation effect. The $\alpha$-factor can be found from the relation\textsuperscript{22}

$$\alpha = -\frac{2\pi}{\delta n \cdot L} \cdot \frac{\Delta \lambda / \Delta I}{\Delta g_{\text{net}} / \Delta I},$$

where $\delta n$ is the Fabry–Perot mode spacing, $L$ is the cavity length, $\Delta \lambda / \Delta I$ is the mode wavelength shift with current (equivalent to the change in refractive index with pumping current), and $\Delta g_{\text{net}} / \Delta I$ is the change in net modal gain with current. Figure 3 shows the wavelength $\lambda$ and the shift $\Delta \lambda / \Delta I$ as a function of current, for the lasing mode. In Fig. 3(b), the abscissa of the graph markers is placed at the average of the two current levels used from Fig. 3(a). As the current increases, the wavelength blueshifts at a constant rate $\Delta \lambda / \Delta I \approx 1.5 \times 10^{-3}$ nm/mA for currents below 0.98$I_{\text{th}}$, and then almost stays constant, resulting in a drastic decrease of $|\Delta \lambda / \Delta I|$, which is nearly zero from 0.98$I_{\text{th}}$ to 0.10$I_{\text{th}}$. Figure 4 shows the net modal gain and the differential gain $\Delta g_{\text{net}} / \Delta I$ as a function of current at the lasing wavelength. The net modal gain increases linearly with the increase of current when the current is below 0.91$I_{\text{th}}$, and superlinearly above. Correspondingly, $\Delta g_{\text{net}} / \Delta I$ is almost a constant below 0.91$I_{\text{th}}$, and then increases significantly. These trends are in contrast to the current dependence of differential gain in similar-design InGaAs/GaAs QW lasers, which was presented in Ref. 23. In QW lasers, the differential gain was found to be the highest at low current density, gradually decreasing with increasing the carrier density as the states associated with the $n=1$ transition fill. In addition, no saturation of the gain and the differential gain is observed below $I_{\text{th}}$ in our SML-grown QD lasers, while saturation is very pronounced for typical SK-grown QD lasers\textsuperscript{16,17} when the current is near to the threshold.

![FIG. 2. Net modal gain spectra of an SML InGaAs/GaAs QD laser at different injection currents.](image)

![FIG. 3. Wavelength (a) and its shift (b) vs current for the lasing mode.)](image)

![FIG. 4. Net modal gain (a) and differential gain (b) vs current at lasing wavelength.](image)

![FIG. 5. Linewidth enhancement factor at the lasing wavelength as a function of current, for an SML InGaAs/GaAs QD laser.](image)
With the data in Figs. 3(b) and 4(b), the \( \alpha \)-factor is determined as a function of current for the lasing mode, as shown in Fig. 5. It can be seen that the \( \alpha \)-factor decreases to zero when the current increases to 0.98\( I_{\text{th}} \). This is our first observation of a zero linewidth enhancement factor at the lasing wavelength for QD lasers. When the current is very near to the threshold, the carrier–carrier scattering (Auger process) will be the dominant mechanism of carrier capture and relaxation, and the population probability for all the QDs is almost the same, resulting in a very symmetric gain spectrum. In this case, the differential gain is also symmetric to the peak gain energy position where lasing occurs. Thus, the change of the differential refractive index computed via the Kramers–Kronig relation is exactly zero at the lasing energy (i.e., the peak gain position). For SK QD lasers with a single sheet of QDs, the ground states of QDs can be easily saturated due to the lower density of QDs. The contribution of excited states or wetting-layer states to the gain might cause an asymmetric gain curve, which increases the linewidth enhancement factor in an SML InGaAs/GaAs QD laser diode. These properties are attributed to the high density of SML QDs in our devices.

In summary, we have observed a narrow gain spectrum, high modal gain, the increasing differential gain, and zero-linewidth enhancement factor in an SML InGaAs/GaAs QD laser diode. These properties are attributed to the high density and the high uniformity of SML QDs in our devices and they are very promising for the application of SML QDs in high-power lasers.

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